

COPY OF PAPERS
ORIGINALLY FILED

SHEET 1 OF 1

#2105
Oliver
5/9/02

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
MICRON.133DV1APPLICATION NO.
10/038,305O I P E INFORMATION DISCLOSURE STATEMENT
BY APPLICANT

MAR 1 2 2002

(USE SEVERAL SHEETS IF NECESSARY)

APPLICANT
Trivedi et al.FILING DATE
January 2, 2002GROUP
281B

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
TN	1.	4,804,560	2/14/89	Shioya et al.	—	—	—
↑	2.	5,677,237	10/14/97	Tsai et al.	—	—	—
	3.	5,714,804	2/3/98	Miller et al.	—	—	—
TN	4.	5,840,625	11/24/98	Feldner	—	—	—

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
TN	5.	JP 8227939 Abstract	9/3/96	Japan	—	—	x	
✓	6.	JP 9532478 Abstract	2/21/95	Japan	—	—	x	
TN								

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
TN	7.	Miller et al., "CVD Tungsten Interconnect and Contact Barrier Technology for VLSI," Solid State Technology, Dec. 1982, pp. 85-90.
TN	8.	Saraswat, et al. "Selective CVD of Tungsten for VLSI Technology," Journal of the Electrochemical Society, Vol. 131, No. 3, 1984, pp. 409-419.
TN	9.	Stacy et al. "Interfacial Structure of Tungsten Layers Formed by Selective Low Pressure Chemical Vapor Deposition," J. Electrochem. Soc.: Solid State Science and Technology, Vol. 132, No. 2, Feb. 1985, pp. 444-448.

W:\DOCS\ZYW\ZYW-1043.DOC
030702

EXAMINER	DATE CONSIDERED
<i>[Signature]</i>	7/31/02
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	